

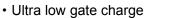
isc N-Channel MOSFET Transistor

IPI50R299CP

• FEATURES

- Static drain-source on-resistance:
 R_{DS}(on) ≤0.299Ω
- Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION



High peak current capability

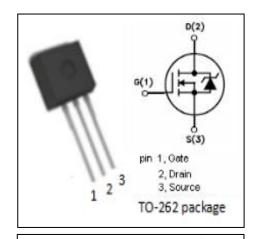


• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	500	V
V _{GS}	Gate-Source Voltage	±20	V
Ι _D	Drain Current-Continuous	12	Α
I _{DM}	Drain Current-Single Pulsed	26	А
P _D	Total Dissipation @Tc=25°C	104	W
Tj	Max. Operating Junction Temperature	150	$^{\circ}\mathbb{C}$
T _{stg}	Storage Temperature	-55~150	${\mathbb C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	1.2	°C/W	



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- G b2	100	A		
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	DIM	MIN	MAX	
	A	4.37	4.77	
	A1	1.22	1.42	
	A2	2.47	2.87	
	Ъ	0.70	0.97	
	Ъ2	1.17	1.42	
	С	0.28	0.53	
	D	23.20	24.02	
	D1	8.38	8.90	
	D2	6.00	-8	
	E	9.90	10.39	
	E4	7.30	-	
	е	2.5	4BSC	
	G	1.25	1.50	
	H2	(1.31	
	L	13.34	14.10	
	L1	3.30	4.06	

isc website: www.iscsemi.cn

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =250 μ A	500			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =0.44mA	2.5		3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =6.6A			0.299	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V;V _{DS} =0V			0.1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} =500V; V _{GS} = 0V			1	μА
V _{SD}	Diode forward voltage	IF=6.6A; V _{GS} = 0V			1.2	V

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